Standard Frequency Differential Oscillator



Features

- 31 standard frequencies from 25 MHz to 212.5 MHz
- LVPECL and LVDS output signaling types
- 0.6 ps RMS phase jitter (random) over 12 kHz to 20 MHz bandwidth
- Frequency stability as low as ±10 ppm
- Industrial and extended commercial temperature ranges
- Industry-standard packages: 3.2x2.5, 5.0x3.2 and 7.0x5.0 mmxmm
- For any other frequencies between 1 to 625 MHz, refer to SiT9121 and SiT9122 datasheet

Applications

- 10GB Ethernet, SONET, SATA, SAS, Fibre Channel, **PCI-Express**
- Telecom, networking, instrumentation, storage, servers







Electrical Characteristics

Parameter and Conditions	Symbol	Min.	Тур.	Max.	Unit	Condition
	L	VPECL an	d LVDS, C	ommon El	ectrical C	Characteristics
Supply Voltage	Vdd	2.97	3.3	3.63	V	
		2.25	2.5	2.75	V	
		2.25	-	3.63	V	Termination schemes in Figures 1 and 2 - XX ordering code
Output Frequency Range	f	25	-	212.5	MHz	See last page for list of standard frequencies
Frequency Stability	F_stab	-10	ı	+10	ppm	
		-20	_	+20	ppm	Inclusive of initial tolerance, operating temperature, rated power
		-25	_	+25	ppm	supply voltage, and load variations
		-50	_	+50	ppm	
First Year Aging	F_aging1	-2	-	+2	ppm	25°C
10-year Aging	F_aging10	-5	_	+5	ppm	25°C
	T_use	-40	-	+85	°C	Industrial
Operating Temperature Range		-20	_	+70	°C	Extended Commercial
Input Voltage High	VIH	70%	_	_	Vdd	Pin 1, OE or ST
Input Voltage Low	VIL	_	_	30%	Vdd	Pin 1, OE or ST
Input Pull-up Impedance	Z_in	-	100	250	kΩ	Pin 1, OE logic high or logic low, or ST logic high
		2	_	_	ΜΩ	Pin 1, ST logic low
Start-up Time	T_start	-	6	10	ms	Measured from the time Vdd reaches its rated minimum value.
Resume Time	T_resume	-	6	10	ms	In Standby mode, measured from the time \$\overline{ST}\$ pin crosses 50% threshold.
Duty Cycle	DC	45	_	55	%	Contact SiTime for tighter duty cycle
		L\	/PECL, DO	and AC C	haracter	istics
Current Consumption	ldd	-	61	69	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V
OE Disable Supply Current	I_OE	_	_	35	mA	OE = Low
Output Disable Leakage Current	I_leak	_	_	1	μΑ	OE = Low
Standby Current	I_std	-	_	100	μΑ	ST = Low, for all Vdds
Maximum Output Current	I_driver	_	_	30	mA	Maximum average current drawn from OUT+ or OUT-
Output High Voltage	VOH	Vdd-1.1	-	Vdd-0.7	V	See Figure 1(a)
Output Low Voltage	VOL	Vdd-1.9	-	Vdd-1.5	V	See Figure 1(a)
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	V	See Figure 1(b)
Rise/Fall Time	Tr, Tf	_	300	500	ps	20% to 80%, see Figure 1(a)
OE Enable/Disable Time	T_oe	-	_	115	ns	f = 212.5 MHz - For other frequencies, T_oe = 100ns + 3 period
RMS Period Jitter	T_jitt	-	1.2	1.7	ps	f = 100 MHz, VDD = 3.3V or 2.5V
		-	1.2	1.7	ps	f = 156.25 MHz, VDD = 3.3V or 2.5V
DMO DL L'W (L	T 15	-	1.2	1.7	ps	f = 212.5 MHz, VDD = 3.3V or 2.5V
RMS Phase Jitter (random)	T_phj	-	0.6	0.85	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds
		ı	VDS, DC	and AC Ch	aracteris	
Current Consumption	ldd	-	47	55	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V
OE Disable Supply Current	I_OE	-	_	35	mA	OE = Low
Differential Output Voltage	VOD	250	350	450	mV	See Figure 2

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Standard Frequency Differential Oscillator

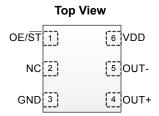


Electrical Characteristics (continued)

Parameter and Conditions	Symbol	Min.	Тур.	Max.	Unit	Condition				
LVDS, DC and AC Characteristics (continued)										
Output Disable Leakage Current I_leak - 1 μA OE = Low										
Standby Current	I_std	-	-	100	μΑ	ST = Low, for all Vdds				
VOD Magnitude Change	ΔVOD	_	-	50	mV	See Figure 2				
Offset Voltage	VOS	1.125	1.2	1.375	V	See Figure 2				
VOS Magnitude Change	ΔVOS	-	-	50	mV	See Figure 2				
Rise/Fall Time	Tr, Tf	-	495	600	ps	20% to 80%, see Figure 2				
OE Enable/Disable Time	T_oe	ı	-	115	ns	f = 212.5 MHz - For other frequencies, T_oe = 100ns + 3 period				
RMS Period Jitter	T_jitt	-	1.2	1.7	ps	f = 100 MHz, VDD = 3.3V or 2.5V				
		-	1.2	1.7	ps	f = 156.25 MHz, VDD = 3.3V or 2.5V				
	- 1.2 1.7 ps f = 212.5 MHz, VDD = 3.3V or 2.5V									
RMS Phase Jitter (random)	T_phj	·	0.6	0.85	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds				

Pin Description

Pin	Мар		Functionality
	OE	Input	H or Open: specified frequency output L: output is high impedance
1	ST	Input	H or Open: specified frequency output L: Device goes to sleep mode. Supply current reduces to I_std.
2	NC	NA	No Connect; Leave it floating or connect to GND for better heat dissipation
3	GND	Power	VDD Power Supply Ground
4	OUT+	Output	Oscillator output
5	OUT-	Output	Complementary oscillator output
6	VDD	Power	Power supply voltage



Absolute Maximum

Attempted operation outside the absolute maximum ratings of the part may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
VDD	-0.5	4	V
Electrostatic Discharge (HBM)	-	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	-	260	°C

Thermal Consideration

Package	θJA, 4 Layer Board (°C/W)	θJC, Bottom (°C/W)
7050, 6-pin	142	27
5032, 6-pin	97	20
3225, 6-pin	109	20

Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method 2002
Mechanical Vibration	MIL-STD-883F, Method 2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method 2003
Moisture Sensitivity Level	MSL1 @ 260°C



Waveform Diagrams

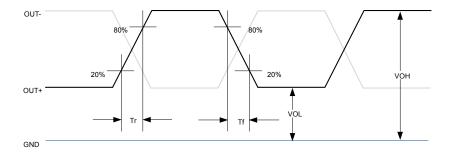


Figure 1(a). LVPECL Voltage Levels per Differential Pin (OUT+/OUT-)

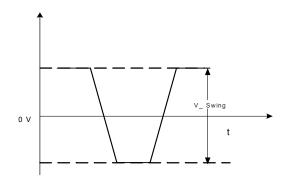


Figure 1(b). LVPECL Voltage Levels Across Differential Pair

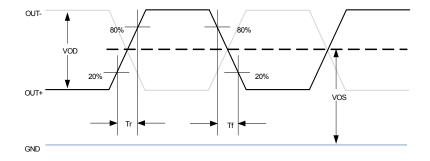


Figure 2. LVDS Voltage Levels per Differential Pin (OUT+/OUT-)



Termination Diagrams

LVPECL:

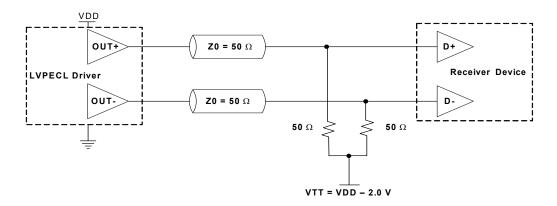


Figure 3. LVPECL Typical Termination

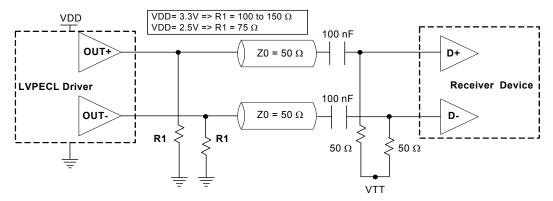


Figure 4. LVPECL AC Coupled Termination

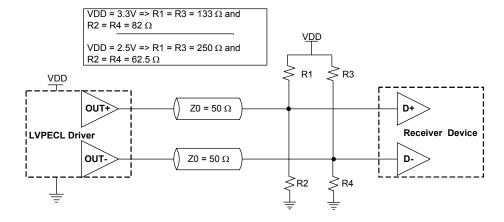


Figure 5. LVPECL with Thevenin Typical Termination

Standard Frequency Differential Oscillator



LVDS:

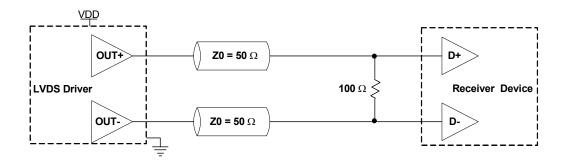
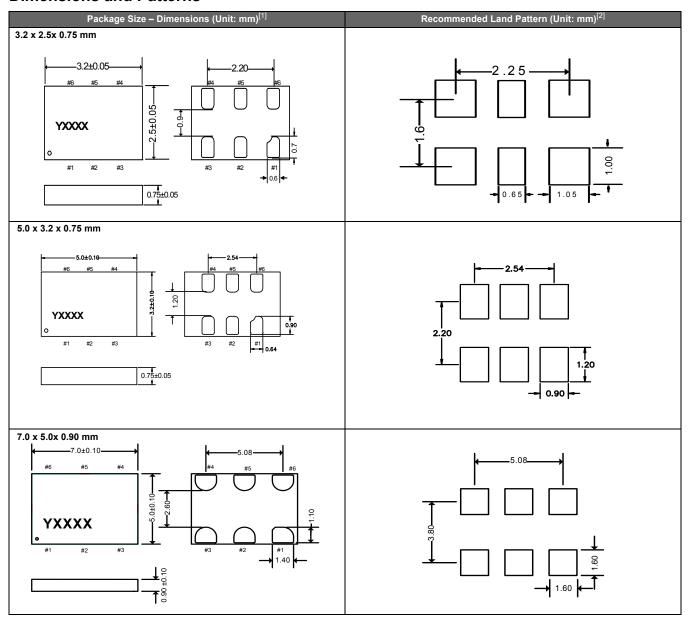


Figure 6. LVDS Single Termination (Load Terminated)

Standard Frequency Differential Oscillator



Dimensions and Patterns



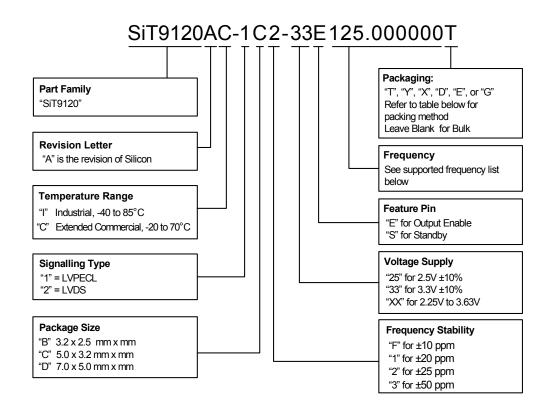
Notes:

- 1. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
- 2. A capacitor of value 0.1 μF between Vdd and GND is recommended.

Standard Frequency Differential Oscillator



Ordering Information



Supported Frequencies

25.000000 MHz	50.000000 MHz	74.175824 MHz	74.250000 MHz	75.000000 MHz	98.304000 MHz	100.000000 MHz	106.250000 MHz
125.000000 MHz	133.000000 MHz	133.300000 MHz	133.330000 MHz	133.333000 MHz	133.333300 MHz	133.333330 MHz	133.333333 MHz
148.351648 MHz	148.500000 MHz	150.000000 MHz	155.520000 MHz	156.250000 MHz	161.132800 MHz	166.000000 MHz	166.600000 MHz
166.660000 MHz	166.666000 MHz	166.666600 MHz	166.666660 MHz	166.666666 MHz	200.000000 MHz	212.500000 MHz	

Ordering Codes for Supported Tape & Reel Packing Method

Device Size	8 mm T&R (3ku)	8 mm T&R (1ku)	8 mm T&R (250u)	12 mm T&R (3ku)	12 mm T&R (1ku)	12 mm T&R (250u)	16 mm T&R (3ku)	16 mm T&R (1ku)	16 mm T&R (250u)
7.0 x 5.0 mm	_	_	_	-	-	_	Т	Y	Х
5.0 x 3.2 mm	_	_	_	Т	Y	X	_	_	_
3.2 x 2.5 mm	D	Е	G	Т	Y	Х	-	_	_

Standard Frequency Differential Oscillator



Revision History

Version	Release Date	Change Summary
1.01	2/20/13	Original
1.02	11/23/13	Added input specifications, LVPECL/LVDS waveforms, packaging T&R options
1.03	2/6/14	Added 8mm T&R option
1.04	3/3/14	Added ±10 ppm
1.05	7/23/14	Include Thermal Consideration Table
1.06	10/3/14	Modified Thermal Consideration values

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Supplemental Information

The Supplemental Information section is not part of the datasheet and is for informational purposes only.



Silicon MEMS Outperforms Quartz

Silicon MEMS Outperforms Quartz



Best Reliability

Silicon is inherently more reliable than quartz. Unlike quartz suppliers, SiTime has in-house MEMS and analog CMOS expertise, which allows SiTime to develop the most reliable products. Figure 1 shows a comparison with quartz technology.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal™ process, which eliminates foreign particles and improves long term aging and reliability
- · World-class MEMS and CMOS design expertise

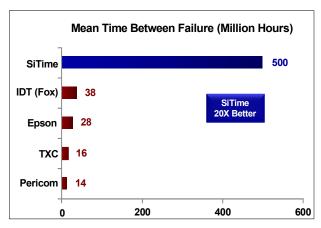


Figure 1. Reliability Comparison^[1]

Best Aging

Unlike quartz, MEMS oscillators have excellent long term aging performance which is why every new SiTime product specifies 10-year aging. A comparison is shown in Figure 2.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal process, which eliminates foreign particles and improves long term aging and reliability
- Inherently better immunity of electrostatically driven MEMS resonator

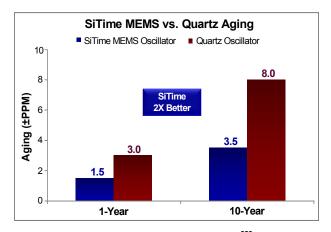


Figure 2. Aging Comparison^[2]

Best Electro Magnetic Susceptibility (EMS)

SiTime's oscillators in plastic packages are up to 54 times more immune to external electromagnetic fields than quartz oscillators as shown in Figure 3.

Why is SiTime Best in Class:

- Internal differential architecture for best common mode noise rejection
- Electrostatically driven MEMS resonator is more immune to EMS

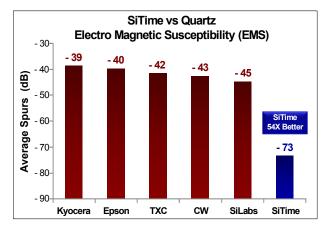


Figure 3. Electro Magnetic Susceptibility (EMS)[3]

Best Power Supply Noise Rejection

SiTime's MEMS oscillators are more resilient against noise on the power supply. A comparison is shown in Figure 4.

Why is SiTime Best in Class:

- On-chip regulators and internal differential architecture for common mode noise rejection
- · Best analog CMOS design expertise

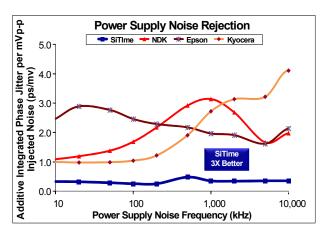


Figure 4. Power Supply Noise Rejection^[4]

Silicon MEMS Outperforms Quartz



Best Vibration Robustness

High-vibration environments are all around us. All electronics, from handheld devices to enterprise servers and storage systems are subject to vibration. Figure 5 shows a comparison of vibration robustness.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than guartz
- Center-anchored MEMS resonator is the most robust design

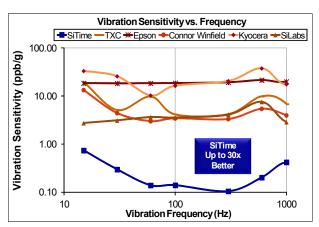


Figure 5. Vibration Robustness^[5]

Notes:

- 1. Data Source: Reliability documents of named companies.
- 2. Data source: SiTime and quartz oscillator devices datasheets.
- 3. Test conditions for Electro Magnetic Susceptibility (EMS):
 - According to IEC EN61000-4.3 (Electromagnetic compatibility standard)
 - Field strength: 3V/m
 - Radiated signal modulation: AM 1 kHz at 80% depth
 - Carrier frequency scan: 80 MHz 1 GHz in 1% steps
 - · Antenna polarization: Vertical
 - DUT position: Center aligned to antenna

Devices used in this test:

SiTime, SiT9120AC-1D2-33E156.250000 - MEMS based - 156.25 MHz

Epson, EG-2102CA 156.2500M-PHPAL3 - SAW based - 156.25 MHz

TXC, BB-156.250MBE-T - 3rd Overtone quartz based - 156.25 MHz

Kyocera, KC7050T156.250P30E00 - SAW based - 156.25 MHz

Connor Winfield (CW), P123-156.25M - 3rd overtone quartz based - 156.25 MHz

SiLabs, Si590AB-BDG - 3rd overtone quartz based - 156.25 MHz

4. 50 mV pk-pk Sinusoidal voltage.

Devices used in this test:

SiTime, SiT8208AI-33-33E-25.000000, MEMS based - 25 MHz

NDK, NZ2523SB-25.6M - quartz based - 25.6 MHz

Kyocera, KC2016B25M0C1GE00 - quartz based - 25 MHz

Epson, SG-310SCF-25M0-MB3 - quartz based - 25 MHz

- 5. Devices used in this test: same as EMS test stated in Note 3.
- 6. Test conditions for shock test:
 - MIL-STD-883F Method 2002
 - Condition A: half sine wave shock pulse, 500-g, 1ms
 - \bullet Continuous frequency measurement in 100 μs gate time for 10 seconds

Devices used in this test: same as EMS test stated in Note 3

7. Additional data, including setup and detailed results, is available upon request to qualified customers. Please contact productsupport@sitime.com.

Best Shock Robustness

SiTime's oscillators can withstand at least $50,000\ g$ shock. They all maintain their electrical performance in operation during shock events. A comparison with quartz devices is shown in Figure 6.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than guartz
- Center-anchored MEMS resonator is the most robust design

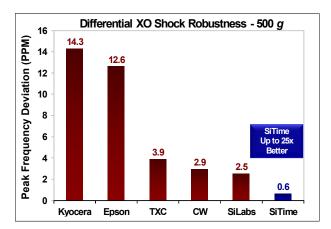


Figure 6. Shock Robustness^[6]

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